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BLC8G24LS-240AV

Power LDMOS transistor
Rev. 5 — 6 January 2016

AMPLEON

Product data sheet

Product profile

1.1 General description

240 W LDMOS packaged asymmetric Doherty power transistor for base station applications at frequencies from 2300 MHz to 2400 MHz.

Table 1. Typical performance

Typical RF performance at $T_{case} = 25 \, ^{\circ}$ C in an asymmetrical Doherty production test circuit. V_{DS} = 28 V; I_{Dq} = 500 mA (main); $V_{GS(amp)peak}$ = 0.30 V, unless otherwise specified.

Test signal	f	V _{DS}	P _{L(AV)}	Gp	η_D	ACPR
	(MHz)	(V)	(W)	(dB)	(%)	(dBc)
1-carrier W-CDMA	2300 to 2400	28	56	15	44	-29 <u>[1]</u>

^[1] Test signal: 3GPP test model 1; 64 DPCH; PAR = 7.2 dB at 0.01% probability on CCDF per carrier.

1.2 Features and benefits

- Excellent ruggedness
- High-efficiency
- Low thermal resistance providing excellent thermal stability
- Designed for broadband operation (2300 MHz to 2400 MHz)
- Asymmetric design to achieve optimum efficiency across the band
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent digital pre-distortion capability
- Internally matched for ease of use
- Integrated ESD protection
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

 RF power amplifiers for base stations and multi carrier applications in the 2300 MHz to 2400 MHz frequency range



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2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	drain2 (peak)	0	
2	drain1 (main)	6 9 [2 ← 6
3	gate1 (main)		7•-
4	gate2 (peak)		3——
5	source [1]	7 8	4 — 1
6	video decoupling (main)		8•-
7	n.c.		9
8	n.c.		1
9	video decoupling (peak)		aaa-009150

^[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Packag	Package				
	Name	Description	Version			
BLC8G24LS-240AV	-	air cavity plastic earless flanged package; 8 leads	SOT1252-1			

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
V_{DS}	drain-source voltage		-	65	V	
V _{GS(amp)main}	main amplifier gate-source voltage		-0.5	+13	V	
V _{GS(amp)peak}	peak amplifier gate-source voltage		-0.5	+13	V	
T _{stg}	storage temperature		-65	+150	°C	
Ti	junction temperature	[1]	-	225	°C	

^[1] Continuous use at maximum temperature will affect the reliability, for details refer to the on-line MTF calculator.

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-c)}		V_{DS} = 28 V; I_{Dq} = 500 mA (main); $V_{GS(amp)peak}$ = 0.30 V; T_{case} = 80 °C; P_L = 56 W	0.26	K/W

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6. Characteristics

Table 6. DC characteristics $T_i = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Main dev	rice					
V _{(BR)DSS}	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 1.44 \text{ mA}$	65	-	-	V
V _{GS(th)}	gate-source threshold voltage	V _{DS} = 10 V; I _D = 144 mA	1.5	1.9	2.3	V
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 30 V	-	-	2.8	μΑ
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 V;$ $V_{DS} = 10 V$	-	27	-	A
I _{GSS}	gate leakage current	V _{GS} = 11 V; V _{DS} = 0 V	-	-	280	nA
9 _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 5.04 A	-	10.10	-	S
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 V;$ $I_D = 5.04 A$	-	100	166	mΩ
Peak dev	rice		1		1	-
V _{(BR)DSS}	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 2.2 \text{ mA}$	65	-	-	V
V _{GS(th)}	gate-source threshold voltage	V _{DS} = 10 V; I _D = 220 mA	1.5	1.9	2.3	V
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 30 V	-	-	2.8	μΑ
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	41	-	A
I _{GSS}	gate leakage current	V _{GS} = 11 V; V _{DS} = 0 V	-	-	280	nA
g _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 7.70 A	-	15.63	-	S
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 V;$ $I_D = 7.7 A$	-	69	112	mΩ

Table 7. RF characteristics

Test signal: 1-carrier W-CDMA; PAR = 7.2 dB at 0.01 % probability on the CCDF; 3GPP test model 1; 1 to 64 DPCH; f_1 = 2300 MHz; f_2 = 2400 MHz; RF performance at V_{DS} = 28 V; I_{Dq} = 500 mA (main); $V_{GS(amp)peak}$ = 0.30 V; T_{case} = 25 °C; unless otherwise specified; in an asymmetrical Doherty production test circuit in 2300 MHz to 2400 MHz.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
G_p	power gain	P _{L(AV)} = 56 W	13.3	14.5	-	dB
RLin	input return loss	P _{L(AV)} = 56 W	-	-10	-6	dB
η_{D}	drain efficiency	P _{L(AV)} = 56 W	38	44	-	%
ACPR	adjacent channel power ratio	P _{L(AV)} = 56 W	-	-29	-25	dBc

7. Test information

7.1 Ruggedness in class-AB operation

The BLC8G24LS-240AV is capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: V_{DS} = 28 V; I_{Dq} = 500 mA (main); $V_{GS(amp)peak}$ = 0.30 V; P_L = 240 W (CW); f = 2300 MHz.

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7.2 Impedance information

Table 8. Typical impedance of main device

Measured load-pull data of main device; $I_{Dq} = 1000 \text{ mA}$; $V_{DS} = 28 \text{ V}$. Typical values unless otherwise specified.

f	Z _S [1]	Z _L [1]	P _L [2]	η _D [2]	G _p [2]		
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)		
Maximum pov	Maximum power load						
2300	1.1 – j3.5	1.6 – j4.4	171	56.20	15.2		
2350	1.6 – j3.6	1.7 – j4.5	178	57.60	15.3		
2400	1.9 – j4.5	1.5 – j4.6	175	55.10	16.0		
Maximum dra	Maximum drain efficiency load						
2300	1.1 – j3.5	3.1 – j3.5	127	65.50	17.1		
2350	1.6 – j3.6	2.7 – j3.3	130	65.30	17.4		
2400	1.9 – j4.5	2.4 – j3.5	131	64.70	18.1		

^[1] Z_S and Z_L defined in Figure 1.

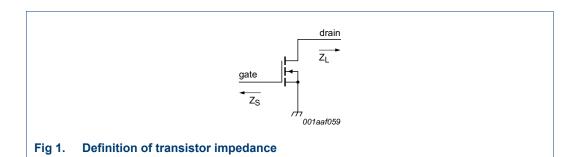
Table 9. Typical impedance of peak device

Measured load-pull data of peak device; I_{Dq} = 1230 mA; V_{DS} = 28 V. Typical values unless otherwise specified.

f	Z _S [1]	Z _L [1]	P _L [2]	η _D [2]	G _p [2]		
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)		
Maximum pov	Maximum power load						
2300	1.0 – j5.3	4.0 – j4.5	252	55.30	16.5		
2350	1.9 – j5.4	3.9 – j4.5	248	55.00	16.1		
2400	2.1 – j6.5	4.6 – j4.5	245	53.80	16.8		
Maximum dra	in efficiency load						
2300	1.0 – j5.3	2.7 – j2.4	190	63.90	18.3		
2350	1.9 – j5.4	2.2 – j2.5	175	63.70	18.1		
2400	2.1 – j6.5	2.3 – j2.7	176	63.00	18.8		

^[1] Z_S and Z_L defined in Figure 1.

^[2] at 3 dB gain compression.



^[2] at 3 dB gain compression.



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7.3 VBW in Doherty operation

The BLC8G24LS-240AV shows 80 MHz (typical) video bandwidth in Doherty test circuit in 2.35 GHz at V_{DS} = 28 V; I_{Dq} = 500 mA and $V_{GS(amp)peak}$ = 0.30 V.

7.4 Test circuit

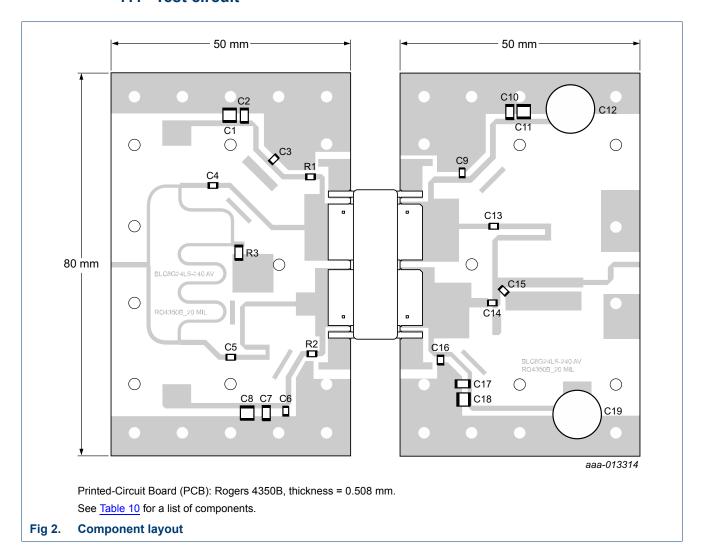


Table 10. List of components For test circuit see Figure 2.

0	B	V. L.	B
Component	Description	Value	Remarks
C1, C8, C11, C18	multilayer ceramic chip capacitor	10 μF	Murata
C2, C7, C10, C17	multilayer ceramic chip capacitor	1 μF	Murata
C3, C4, C5, C6, C9, C13, C14, C16	multilayer ceramic chip capacitor	12 pF	ATC 800B
C12, C19	electrolytic capacitor	2200 μF, 50 V	
C15	multilayer ceramic chip capacitor	0.8 pF	ATC 600F
R1, R2	resistor	9.1 Ω	Vishay Dale: SMD 0805
R3	resistor	50 Ω	Vishay Dale: SMD 0805

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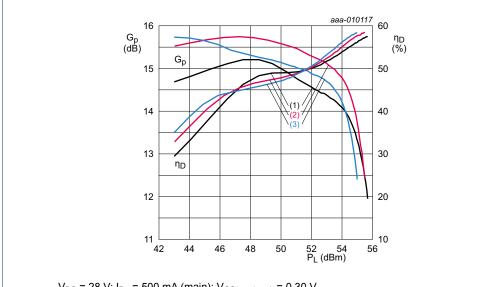
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7.5 Graphical data

7.5.1 Pulsed CW



 $V_{DS} = 28 \text{ V}$; $I_{Dq} = 500 \text{ mA (main)}$; $V_{GS(amp)peak} = 0.30 \text{ V}$.

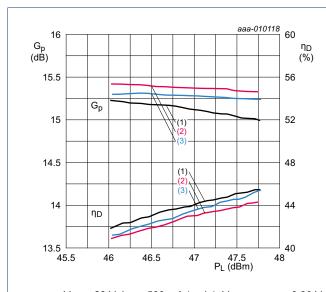
- (1) f = 2300 MHz
- (2) f = 2350 MHz
- (3) f = 2400 MHz

Power gain and drain efficiency as function of output power; typical values

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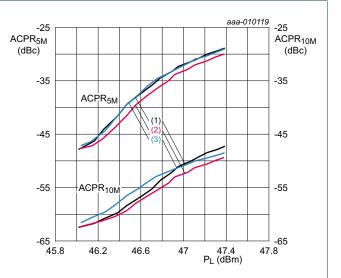
7.5.2 1-Carrier W-CDMA



 V_{DS} = 28 V; I_{Dq} = 500 mA (main); $V_{GS(amp)peak}$ = 0.30 V.

- (1) f = 2300 MHz
- (2) f = 2350 MHz
- (3) f = 2400 MHz

Fig 4. Power gain and drain efficiency as function of output power; typical values

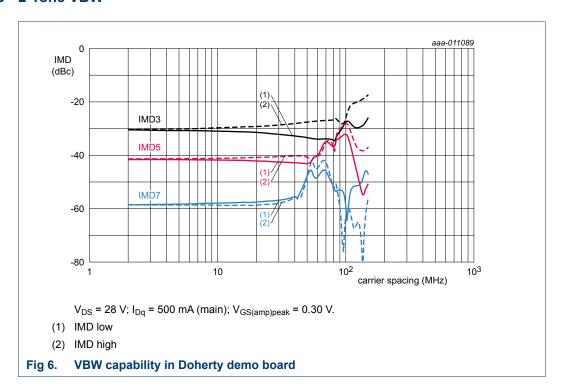


 V_{DS} = 28 V; I_{Dq} = 500 mA (main); $V_{GS(amp)peak}$ = 0.30 V.

- (1) f = 2300 MHz
- (2) f = 2350 MHz
- (3) f = 2400 MHz

Fig 5. Adjacent channel power ratio (5 MHz) and adjacent channel power ratio (10 MHz) as function of output power; typical values

7.5.3 2-Tone VBW



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8. Package outline

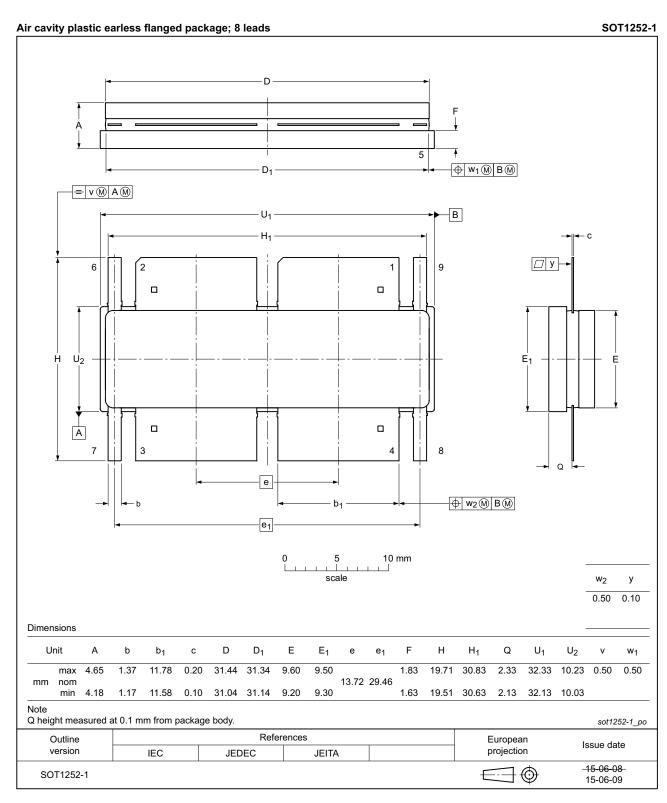


Fig 7. Package outline SOT1252-1



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Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

10. Abbreviations

Table 11. Abbreviations

Acronym	Description			
3GPP	3rd Generation Partnership Project			
CCDF	complementary Cumulative Distribution Function			
CW	Continuous Wave			
DPCH	Dedicated Physical CHannel			
ESD	ElectroStatic Discharge			
LDMOS	Laterally Diffused Metal-Oxide Semiconductor			
MTF	Median Time to Failure			
PAR	Peak-to-Average Ratio			
SMD	Surface Mounted Device			
VBW	Video Bandwidth			
VSWR	Voltage Standing Wave Ratio			
W-CDMA	Wideband Code Division Multiple Access			

11. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BLC8G24LS-240AV v.5	20160106	Product data sheet	-	BLC8G24LS-240AV v.4	
Modifications: • Table 7 on page 3: table has been updated					
BLC8G24LS-240AV v.4	20150901	Product data sheet	-	BLC8G24LS-240AV v.3	
BLC8G24LS-240AV v.3	20150728	Product data sheet	-	BLC8G24LS-240AV v.2	
BLC8G24LS-240AV v.2	20141218	Product data sheet	-	BLC8G24LS-240AV v.1	
BLC8G24LS-240AV v.1	20130926	Objective data sheet	-	-	

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12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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